



#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
30V	1.5Ω @ V <sub>GS</sub> = 4.5V	
	2.0Ω @ V <sub>GS</sub> = 2.5V	0.224
	3.0Ω @ V <sub>GS</sub> = 1.8V	0.22A
	4.5Ω @ V <sub>GS</sub> = 1.5V	

#### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

#### **Applications**

- General Purpose Interfacing Switch
- **Power Management Functions**
- Analog Switch

#### **Features and Benefits**

- Low Package Profile, 0.42mm Maximum Package Height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

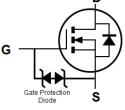
- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (approximate)

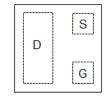




**Bottom View** 







**Equivalent Circuit** 

Top View Package Pin Configuration

## Ordering Information (Note 4)

Part Number	Case	Packaging	
DMN31D5UFZ-7B	X2-DFN0606-3	10K/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



R6 = Product Type Marking Code

Top View Bar Denotes Gate and Source Side



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I <sub>D</sub>	220 150	mA
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	500	mA

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	Steady state	$P_{D}$	393	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	318	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

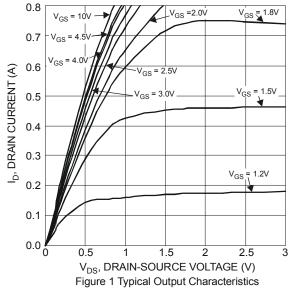
				I			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	1	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C	I <sub>DSS</sub>	_	1	100	nA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_		±10	μA	$V_{GS}$ = ±10V, $V_{DS}$ = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	1	1.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA	
		_	1	2.0		$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1	3.0	Ω	$V_{GS} = 1.8V, I_D = 20mA$	
		_	1	4.5		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA	
		_	2.8	_		V <sub>GS</sub> = 1.2V, I <sub>D</sub> = 1mA	
Diode Forward Voltage	$V_{SD}$	_	0.75	1.0	V	$V_{GS} = 0V$ , $I_S = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	22.2	_	pF		
Output Capacitance	Coss	_	2.9	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.2	_	pF	1 - 1.0WHZ	
Total Gate Charge	Qg	_	0.35	_	nC	V 45V V 45V	
Gate-Source Charge	$Q_{gs}$	_	0.05	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 200 \text{mA}$	
Gate-Drain Charge	$Q_{gd}$	_	0.02	_	nC	- ID - 200IIIA	
Turn-On Delay Time	t <sub>D(on)</sub>	_	3.1	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	2.0	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	20	_	ns	$R_G = 6\Omega$ , $I_D = 200 \text{mA}$	
Turn-Off Fall Time	t <sub>f</sub>	_	6.9	_	ns		

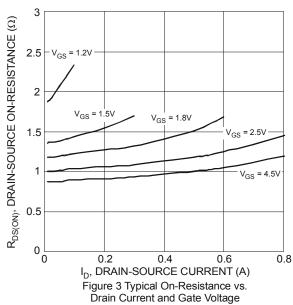
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.







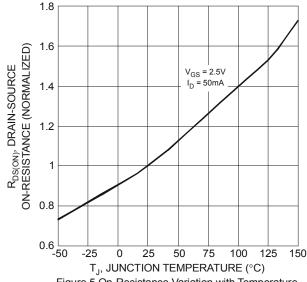
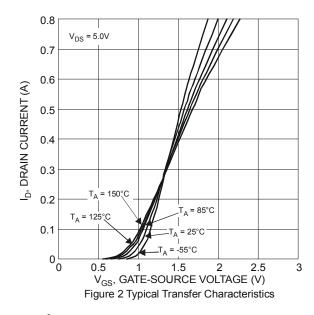
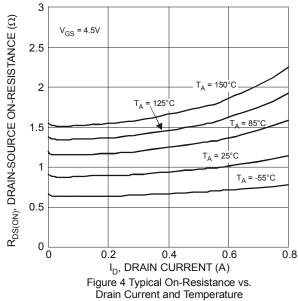


Figure 5 On-Resistance Variation with Temperature





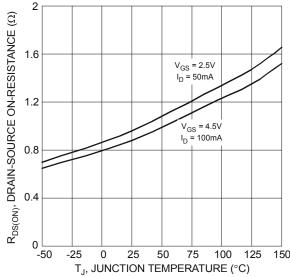


Figure 6 On-Resistance Variation with Temperature





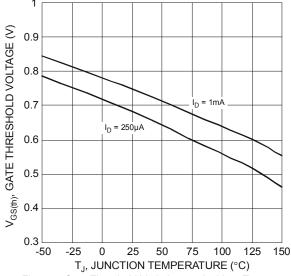
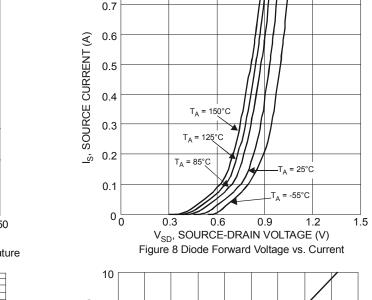
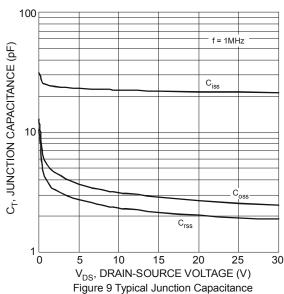
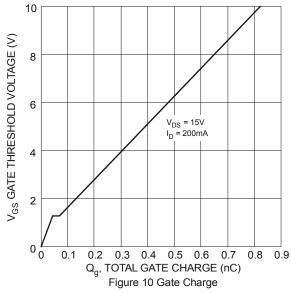


Figure 7 Gate Threshold Variation vs. Ambient Temperature



0.8





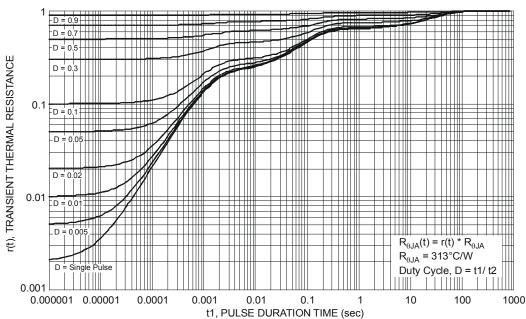
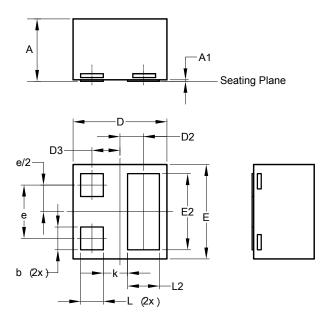


Figure 11 Transient Thermal Resistance



# **Package Outline Dimensions**

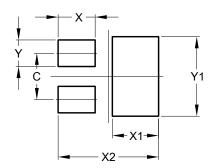
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X2-DFN0606-3					
Dim	Min	Тур			
Α	0.36	0.42	0.39		
A1	0	0.05	0.02		
b	0.10	0.20	0.15		
D	0.57	0.67	0.62		
D2	0.155 BSC				
D3	C	0.185 BSC			
Е	0.57	0.57 0.67			
E2	0.40	0.60	0.50		
е	0.35 BSC				
k	0.16 REF				
Ĺ	0.09	0.21	0.15		
L2	0.11	0.31	0.21		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value		
Difficusions	(in mm)		
С	0.350		
Х	0.280		
X1	0.350		
X2	0.760		
Y	0.200		
Y1	0.600		



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